

Fig. 1

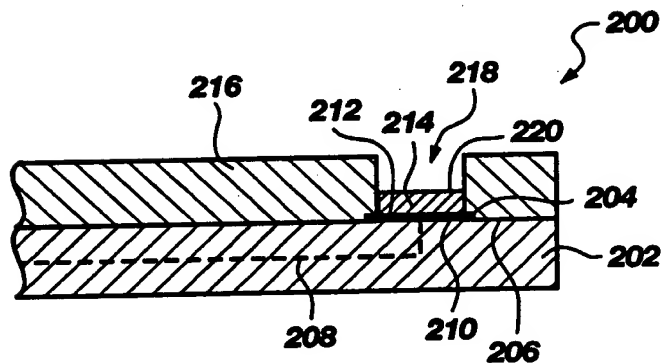


Fig. 2

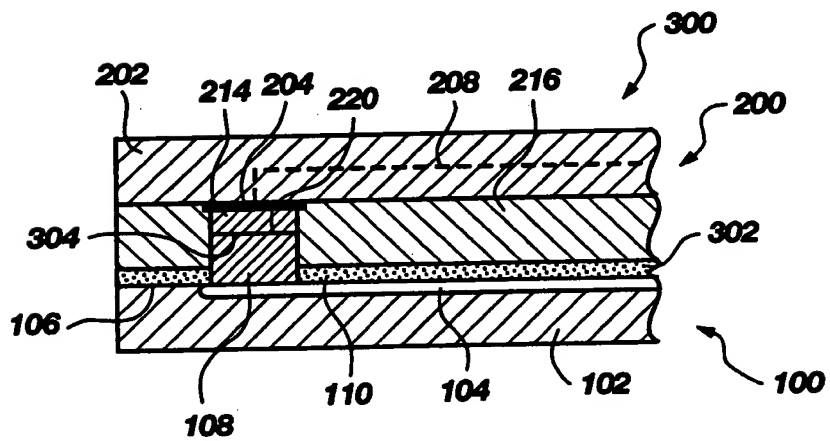


Fig. 3

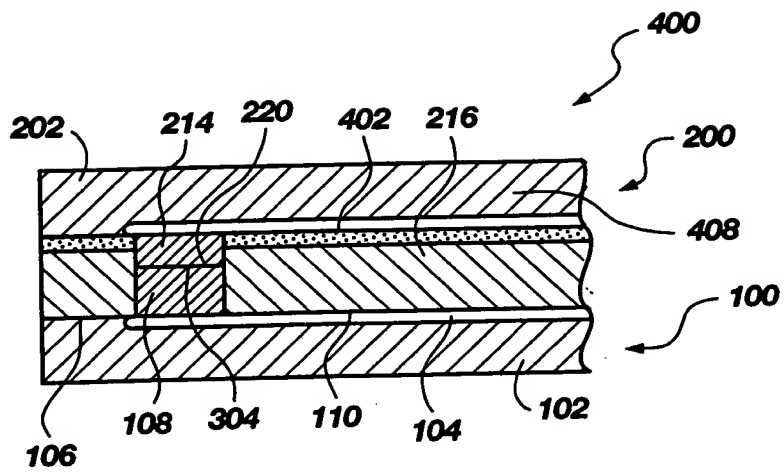


Fig. 4

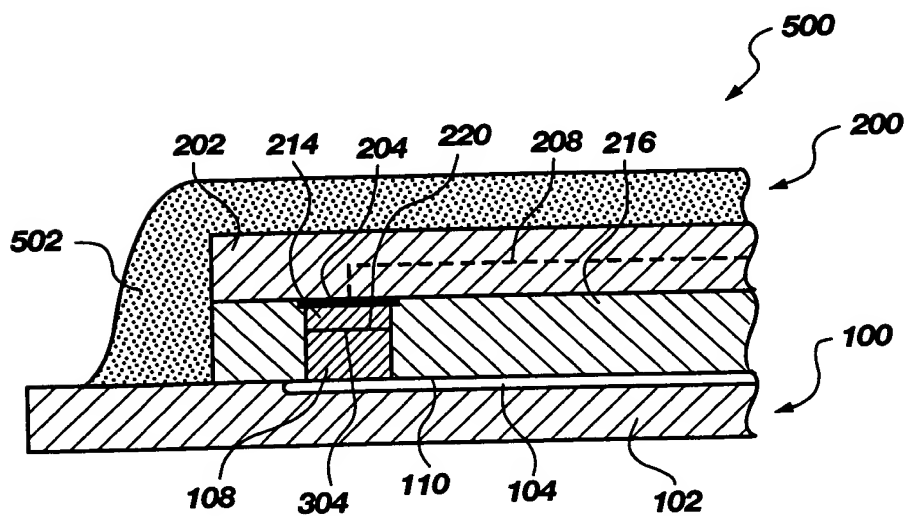


Fig. 5

A cross-sectional view of a multi-layered structure 600. The structure consists of a central core 200 and an outer layer 100. The core 200 is composed of several layers: a top layer 202, a middle layer 204, and a bottom layer 206. The outer layer 100 is composed of a top layer 102, a middle layer 104, and a bottom layer 106. A dashed line 220 is shown within the core 200, and a solid line 214 is shown within the middle layer 204. A small rectangular feature 304 is located within the middle layer 204. A label 602 points to the outer layer 100.

A cross-sectional view of a semiconductor device 700. The device includes a substrate 100 with a top surface 102 and a bottom surface 104. A layer 106 is formed on the top surface 102. A layer 108 is formed on the top surface 102, and a layer 304 is formed on the top surface 102. A layer 200 is formed on the top surface 102, and a layer 206 is formed on the top surface 102. A layer 202 is formed on the top surface 102, and a layer 214 is formed on the top surface 102. A layer 204 is formed on the top surface 102, and a layer 220 is formed on the top surface 102. A layer 208 is formed on the top surface 102, and a layer 704 is formed on the top surface 102. A layer 216 is formed on the top surface 102, and a layer 302 is formed on the top surface 102. A layer 702 is formed on the top surface 102, and a layer 102 is formed on the top surface 102.

Fig. 7